

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI TVV020** is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	8.0 A
<b>V<sub>CEO</sub></b>	35 V
<b>V<sub>CES</sub></b>	60 V
<b>V<sub>EBO</sub></b>	4.0 V
<b>P<sub>DISS</sub></b>	140 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	1.5 °C/W

**PACKAGE STYLE .500 4L STUD**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	1.010 / 25.65	1.050 / 26.67
B	.220 / 5.59	.230 / 5.84
C	.495 / 12.57	.505 / 12.83
D	.003 / 0.08	.007 / 0.18
E	.160 / 4.06	.180 / 4.57
F	.622 / 15.80	
G	.100 / 2.54	.130 / 3.31
H	.415 / 10.54	.425 / 10.80
I	.720 / 18.29	
J	.250 / 6.35	.290 / 7.37

**ORDER CODE: ASI10659**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 50 mA	65			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 50 mA      R <sub>BE</sub> = 10 Ω	60			<b>V</b>
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 50 mA	35			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	4.0			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CB</sub> = 50 V			5.0	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 1.0 A	20		120	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 30 V      f = 1.0 MHz			85	<b>pF</b>
<b>P<sub>G</sub></b>	V <sub>CE</sub> = 25 V      I <sub>C</sub> = 2.5 A      f = 225 MHz	8.0			<b>dB</b>
<b>IMD<sub>3</sub></b>	P <sub>OUT</sub> = 14 W	-51			<b>dBc</b>